5V to 12V Single Buck Voltage Mode PWM Controller

### **Features**

- Wide 5V to 12V Supply Voltage
- Power-On-Reset Monitoring on VCC
- Excellent Output Voltage Regulations
  - 0.6V Internal Reference for JTMA8722/A/D
  - 0.8V Internal Reference for JTMA8722B/C
  - ±0.6% Over-Temperature Range
- Integrated Soft-Start
- Voltage Mode PWM Operation with External Compensation
- Up to 90% Duty Ratio for Fast Transient Response
- Constant Switching Frequency
  - 300kHz ±10% for JTMA8722/B
  - 200kHz ±10% for JTMA8722C
  - 600kHz ±10% for JTMA8722A/D
- Integrated Bootstrap Forward P-CH MOSFET
- 50% Under-Voltage Protection
- 125% Over-Voltage Protection
- Adjustable Over-Current Protection Threshold
  - Using the RDS(ON) of Low-Side MOSFET
- Shutdown Control by COMP
- SOP-8P Package
- Lead Free and Green Devices Available (RoHS Compliant)

### **General Description**

The JTMA8722 is a voltage mode, fixed 200kHz/300kHz/600kHz switching frequency, synchronous buck converter. The JTMA8722 allows wide input voltage that is either a single 5~12V or two supply voltage(s) for various applications. A power-on-reset (POR) circuit monitors the VCC supply voltage to prevent wrong logic controls. A built-in soft-start circuit prevents the output voltages from overshoot as well as limits the input current. An internal 0.6V temperature-compensated reference voltage with high accuracy is designed to meet the requirement of low output voltage applications. The JTMA8722 provides excellent output voltage regulations against load current variation.

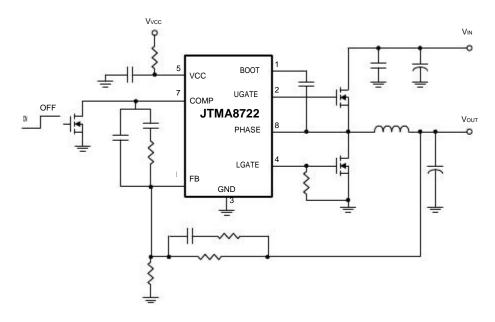
The controller's over-current protection monitors the output current by using the voltage drop across the RDS (ON) of low-side MOSFET, eliminating the need for a current sensing resistor that features high efficiency and low cost. In addition, the JTMA8722 also integrates excellent protection functions. The over-voltage protection (OVP), under-voltage protection (UVP). OVP circuit which monitors the FB voltage to prevent the PWM output from over voltage, and UVP circuit which monitors the FB voltage to prevent the PWM output from under voltage or short circuit. The JTMA8722 is available in SOP-8P packages

# **Applications**

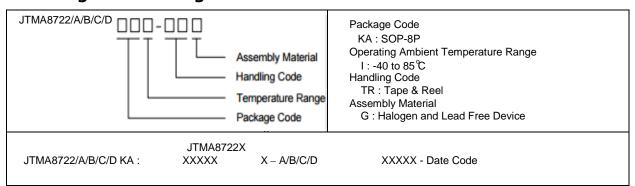
- Graphic Cards
- DSL, Switch HUB
- Wireless Lan
- Notebook Computer
- Mother Board
- LCD Monitor/TV

JIATAIMU reserves the right to make changes to improve reliability or manufacturability without notice, and advise customers to obtain the latest version of relevant information to verify before placing orders.

# **Simplified Application Circuit**



# **Ordering and Marking Information**



Note: JIATAIMU lead-free products contain molding compounds/die attach materials and 100% matte tin plate termination finish; which are fully compliant with RoHS. JIATAIMU lead-free products meet or exceed the lead-free requirements of IPC/JEDEC J-STD-020D for MSL classification at lead-free peak reflow temperature. JIATAIMU defines "Green" to mean lead-free (RoHS compliant) and halogen free (Br or Cl does not exceed 900ppm by weight in homogeneous material and total of Br and Cl does not exceed 1500ppm by weight).

# **Pin Configuration**



# **Absolute Maximum Ratings** (Note 1)

Symbol	Parameter		Rating	Unit
Vvcc	VCC Supply Voltage (VCC to GND)		-0.3 ~ 16	V
Vвоот	BOOT Supply Voltage (BOOT to PHASE)	-0.3 ~ 16	V	
<b>V</b> BOOT	BOOT Supply Voltage (BOOT to GND)		-0.3 ~ 32	V
Vugate	UGATE Voltage (UGATE to PHASE) > 20ns		-0.3 ~ VBOOT+0.3	V
VOGATE	OUNTE VOILAGE (OUNTE LOTTINGE)	< 20ns	-5 ~ VBOOT+5	V
VLGATE	LGATE Voltage (LGATE to GND)	> 20ns	-0.3 ~ Vvcc+0.3	V
VLGATE	< 20ns	< 20ns	-5 ~ Vvcc+5	V
VPHASE	PHASE Voltage (PHASE to GND)	> 20ns	-0.3 ~ 16	V
V FHASE	TTWOE VOILEGE (TTWOE TO CIVE)	< 20ns	-5 ~ 25	V
	FB ,COMP to GND		-0.3 ~ 7	V
	POK to GND	-0.3~Vcc+0.3	V	
TJ	Maximum Junction Temperature	150	°C	
Тѕтс	Storage Temperature	-65 ~ 150	°C	
Tsdr	Maximum Lead Soldering Temperature, 10 Seconds		260	°C

Note1: Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

### **Thermal Characteristics**

S	ymbol	Parameter	Typical Value	Unit
	AL	Thermal Resistance -Junction to Ambient (Note 2) SOP-8P	60	°C/W

Note 2: \( \( \text{J}\_A \) is measured with the component mounted on a high effective thermal conductivity test board in free air.

# **Recommended Operating Conditions** (Note 3)

Symbol	Parameter	Range	Unit
Vvcc	VCC Supply Voltage (VCC to GND)	4.5 ~ 13.2	V
Vоит	Converter Output Voltage for JTMA8722/A/D	0.6 ~ 5	V
<b>V</b> 001	Converter Output Voltage for JTMA8722B/C	0.8 ~ 5	V
VIN	Converter Input Voltage	3~13.2	V
Іоит	Converter Output Current	0 ~ 25	Α
TA	Ambient Temperature	-40 ~ 85	°C
TJ	Junction Temperature	-40 ~ 125	°C

Note 3: Refer to the application circuit for further information.

# **Electrical Characteristics**

Refer to the typical application circuit. These specifications apply over  $V_{VCC} = 12V$ ,  $T_A = -40$ °C to 85°C, unless otherwise noted. Typical values are at  $T_A = 25$ °C.

Symbol	Parameter	rameter Test Conditions		JTMA872	22	Unit
Cymbol	i didilictor	rest conditions	Min.	Тур.	Max.	
INPUT SU	IPPLY VOLTAGE AND CURRENT					
Ivcc	VCC Supply Current (Shutdown Mode)	UGATE and LGATE open; COMP=GND	-	-	550	∞A
	VCC Supply Current	UGATE and LGATE open	-	2.5	10	mA
POWER-0	ON-RESET(POR)		•	•		
	Rising VCC POR Threshold		3.8	4.1	4.4	V
	VCC POR Hysteresis		0.3	0.5	0.6	V
OSCILLA	TOR				1	
		For JTMA8722/B	270	300	330	
Fosc	Oscillator Frequency	For JTMA8722C	180	200	220	kHz
		For JTMA8722A/D	540	600	660	
□Vosc	Oscillator Sawtooth Amplitude (Note 4)	(1.2V~2.7V typical)	-	1.5	-	V
DMAX	Maximum Duty Cycle		-	-	90	%
REFEREN	NCE		<b> </b>	I.		
.,	JTMA8722/A/D Reference Voltage	T <sub>A</sub> = -40 ~ 85°C	0.596	0.6	0.604	V
VREF	JTMA8722B/C Reference Voltage	T <sub>A</sub> = -40 ~ 85°C	0.795	0.8	0.805	V
ERROR A	MPLIFIER			I		
	Open-Loop GAIN (Note 4)	RL = 10k&, CL = 10pF	-	90	-	dB
	Open-Loop Bandwidth (Note 4)	R <sub>L</sub> = 10k&, C <sub>L</sub> = 10pF	-	20	-	MHz
	FB Input Leakage Current	V <sub>FB</sub> = 0.6V	-	-	0.1	∞A
GATE DR	IVERS		I	I.		
	High-side Gate Driver Source Current	VBOOT= 12V, VUGATE-PHASE = 6V	-	1.0	-	
	High-side Gate Driver Sink Current	VBOOT= 12V, VUGATE-PHASE = 6V	-	1.1	-	
	Low-side Gate Driver Source Current	Vvcc = 12V, VLGATE-GND = 6V	-	1.8	-	Α
	Low-side Gate Driver Sink Current	Vvcc = 12V, VLGATE-GND = 6V	-	2.0	-	
TD	Dead-time (Note 4)		-	30	-	ns
PROTEC	TIONS		I	I.		
V <sub>FB_UV</sub>	FB Under-Voltage Protection Trip Point	Percentage of VREF	45	50	55	%
	Under-Voltage Debounce Interval		-	2	-	∞s
	Under-Voltage Protection Enable Delay		-	1.5	-	ms
V <sub>FB_OV</sub>	FB Over-Voltage Protection Rising Threshold	V <sub>FB</sub> rising	120	125	130	%
	FB Over-Voltage Protection Falling Threshold	V <sub>FB</sub> falling	100	105	110	%
	Over-Voltage Debounce Interval		-	2	-	∞s
VOCP_MAX	Built-in Maximum OCP Voltage		-	1200	-	mV
locset	OCSET Current Source		9	10	11	∝A

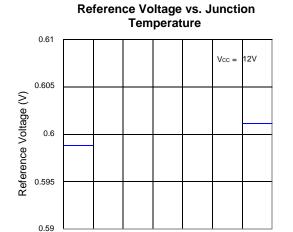
# **Electrical Characteristics (Cont.)**

Refer to the typical application circuit. These specifications apply over  $V_{VCC} = 12V$ ,  $T_A = -40$ °C to 85°C, unless otherwise noted. Typical values are at  $T_A = 25$ °C.

Symbol	Parameter	Test Conditions	,	JTMA872	22 Unit		
Cymbol	r drameter	rest conditions	Min.	Тур.	Max.	O.I.I.	
SOFT-ST	SOFT-START						
VDISABLE	Shutdown Threshold of VCOMP		-	-	0.4	V	
Tss	Internal Soft-Start Interval (Note 4)		-	1.5		ms	

Note 4: Guaranteed by design, not production tested.

# **Typical Operating Characteristics**



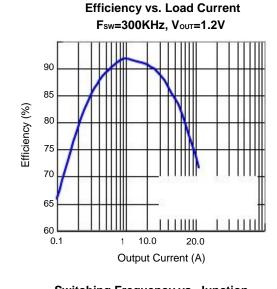
Junction Temperature (°C)

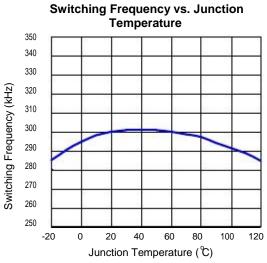
100

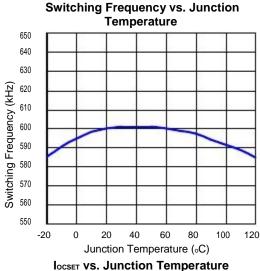
120

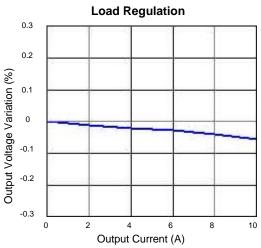
-20

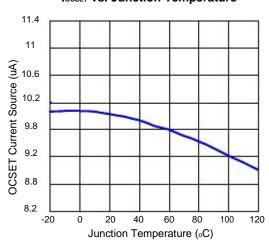
0









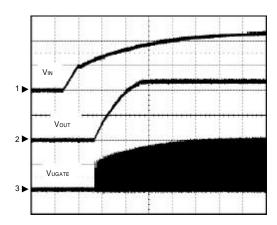


# JTMA8722/A/B/C/D

# **Operating Waveforms**

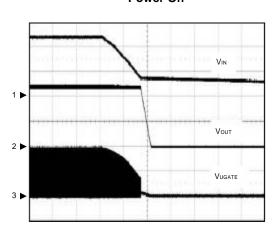
Refer to the typical application circuit. The test condition is V<sub>IN</sub>=12V, T<sub>A</sub>= 25₀C unless otherwise specified.

### **Power On**



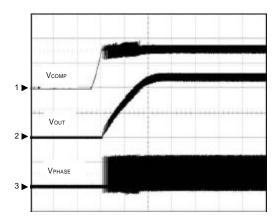
CH1: V<sub>IN</sub>, 5V/Div CH2: V<sub>OUT</sub>, 500mV/Div CH3: V<sub>UGATE</sub>, 10V/Div TIME: 1ms/Div

### **Power Off**



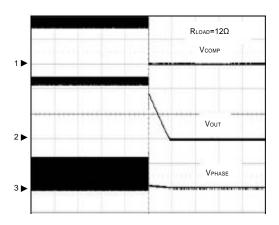
CH1: VIN, 5V/Div CH2: VOUT, 500mV/Div CH3: VUGATE, 10V/Div TIME: 50ms/Div

### **Enable**



CH1: VEN, 5V/Div, DC CH2: VOUT, 500mV/Div, DC CH3: VPHASE, 10V/Div, DC TIME: 1ms/Div

### Shutdown



CH1: VCOMP, 1V/Div CH2: VOUT, 500mV/Div CH3: VPHASE, 10V/Div TIME: 10ms/Div

# **Operating Waveforms**

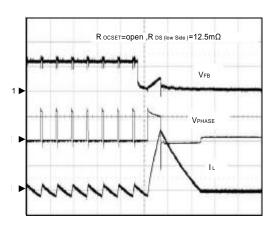
Refer to the typical application circuit. The test condition is  $V_{IN}=12V$ ,  $T_A=25$ <sub>o</sub>C unless otherwise specified.

### **Over-Current Protection**

# Vout UVP UVP UVP 1 OCP IL

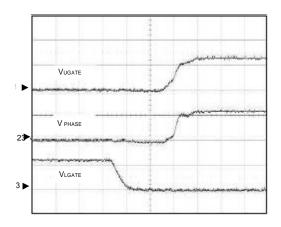
CH1: Vout, 500mV/Div CH2: IL,10A/Div TIME: 20ms/Div

### **Under-Voltage Protection**



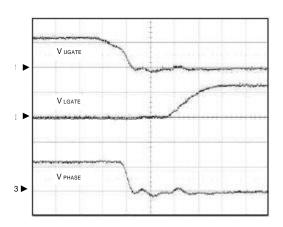
CH1: V<sub>FB</sub>, 200mV/Div CH2: V<sub>PHASE</sub>,10V/Div CH3: I<sub>L</sub>,10A/Div TIME: 10us/Div

### **UGATERising**



CH1: VUGATE, 20V/Div CH2: VLGATE, 10V/Div CH3: VPHASE, 10V/Div TIME: 20ns/Div

### **UGATEFalling**

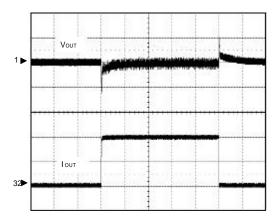


CH1: VUGATE, 20V/Div CH2: VLGATE, 10V/Div CH3: VPHASE, 10V/Div TIME: 20ns/Div

# **Operating Waveforms**

Refer to the typical application circuit. The test condition is  $V_{IN}=12V$ ,  $T_A=25$ <sub>0</sub>C unless otherwise specified.

### **Load Transient**

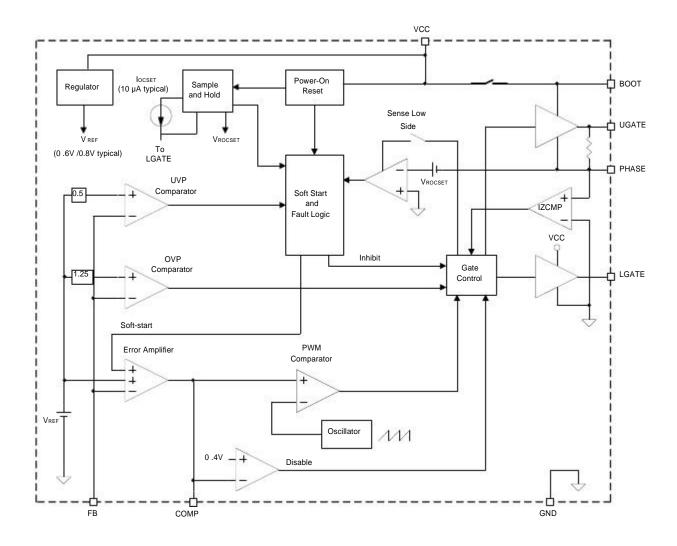


CH1: Vout, 50mV/Div,AC CH2: Iout, 5A/Div TIME: 200us/Div

# **Pin Description**

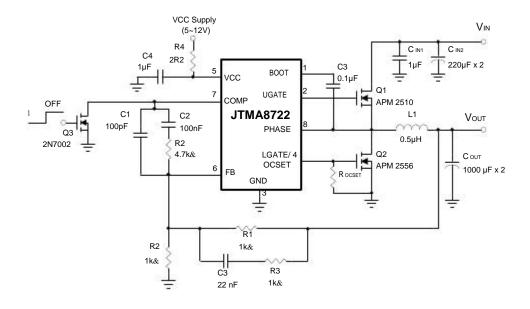
	PIN		
	No. Name		Function Description
JTMA8722A	JTMA8722/B/C/D	Name	
1	1	BOOT	This pin provides the bootstrap voltage to the high-side gate driver for driving the N-channel MOSFET. An external capacitor from PHASE to BOOT, an internal switch generates the bootstrap voltage for the high-side gate driver (UGATE).
2	2	UGATE	High-side Gate Driver Output. This pin is the gate driver for high-side MOSFET.
-	3	GND	Signal and Power ground. Connecting this pin to system ground.
3	-	OCSET	Current-Limit Threshold Setting Pin. There is an internal source current 10uA through a resistor from OCSET pin to GND. This pin is used to monitor the voltage drop across the Drain and Source of the low-side MOSFET for current-limit
4	-	LGATE	Output of The Low-side MOSFET Driver. Connect this pin to the low-side MOSFET.
-	4	LGATE/ OCSET	Low-side Gate Driver Output and Over-Current Setting Input. This pin is the gate driver for low-side MOSFET. It also used to set the maximum inductor current. Refer to the section in "Function Description" for detail.
5	5	VCC	Power Supply Input. Connect a nominal 5V to 12V power supply voltage to this pin. A power-on reset function monitors the input voltage at this pin. It is recommended that a decoupling capacitor (1 to 10µF) be connected to GND for noise decoupling.
6	6	FB	Feedback Input of Converter. The converter senses feedback voltage via FB and regulates the FB voltage at 0.6V/0.8V. Connecting FB with a resistor-divider from the output sets the output voltage of the converter.
7	7	COMP	This is a multiplexed pin. During soft-start and normal converter operation, this pin represents the output of the error amplifier. It is used to compensate the regulation control loop in combination with the FB pin.  Pulling COMP low (Vdisable = 0.4V max.) will shut down the controller.  When the pull-down device is released, the COMP pin will start to rise.  When the COMP pin rises above the Vdisable trip point, the JTMA8722 will begin a new initialization and soft-start cycle.
8	8	PHASE	This pin is the return path for the high-side gate driver. Connecting this pin to the high-side MOSFET source and connect a capacitor to BOOT for the bootstrap voltage. This pin is also used to monitor the voltage drop across the low-side MOSFET for over-current protection.
9 (Exposed Pad)	9 (Exposed Pad)	GND	Thermal Pad. Connect this pad to the system ground plan for good thermal conductivity.

# **Block Diagram**

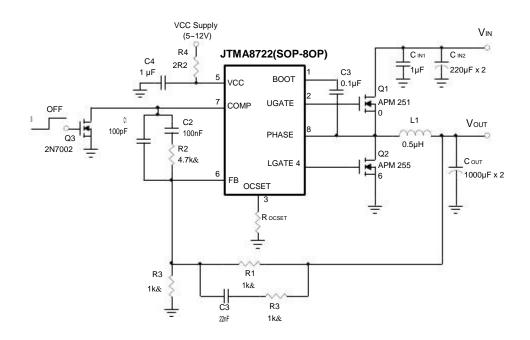


# **Typical Application Circuit**

### For JTMA8722/B/C/D



### For JTMA8722A



# **Function Description**

### Power-On-Reset (POR)

The Power-On-Reset (POR) function of JTMA8722 continually monitors the input supply voltage (VCC) and ensures that the IC has sufficient supply voltage and can work well. The POR function initiates a soft-start process while the VCC voltage just exceeds the POR threshold; the POR function also inhibits the operations of the IC while the VCC voltage falls below the POR threshold.

### Soft-Start

The JTMA8722 builds in a soft-start function about 1.5ms (Typ.) interval, which controls the output voltage rising as well as limiting the current surge at the start-up. During soft-start, an internal ramp voltage connected to the one of the positive inputs of the error amplifier replaces the reference voltage (0.6V typical) until the ramp voltage reaches the reference voltage. The soft-start circuit interval is shown as figure 1.

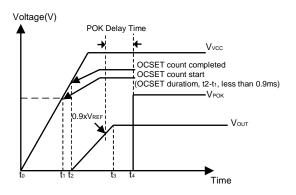


Figure 1. Soft-Start Interval

### **Over-Current Protection of the PWM Converter**

The over-current function protects the switching converter against over-current or short-circuit conditions. The controller senses the inductor current by detecting the drainto-source voltage which is the product of the inductor's current and the on-resistance of the low-side MOSFET during it's on-state. This method enhances the converter's efficiency and reduces cost by eliminating a current sensing resistor required.

A resistor (Rocset), connected from the LGATE/OCSET to GND, programs the over-current trip level. Before the IC initiates a soft-start process, an internal current source,

locset (10 $\propto$ A typical), flowing through the Rocset develops a voltage (VROCSET) across the ROCSET. The device holds VROCSET and stops the current source locset during normal operation. When the voltage across the low-side MOSFET exceeds the VROCSET, the JTMA8722 turns off the high-side and low-side MOSFET, and the device will enters hiccup mode until the over-current phenomenon is released.

For avoid large inductor current occurring in short circuit before power on, the controller reduces internal current source, locset, to half during soft start time. It means that when JTMA8722 is in soft start interval, the internal current source, locset, is only  $5 \times A$  (typical).

The JTMA8722 has an internal OCP voltage, Vocp\_MAX, and the value is 1.2V (typical). When the Rocset x locset exceed 1.2V or the Rocset is floating or not connected, the Vrocset will be the default value 1.2V. The over current threshold would be 1.2V across low-side MOSFET. The threshold of the valley inductor current-limit is therefore given by:

$$|\text{LIMIT} = \frac{2 \cdot \text{IOCSET} \cdot \text{ROCSET}}{\text{RDS(ON) (Iow } \square \text{ side)}}$$

For the over-current is never occurred in the normal operating load range, the variation of all parameters in the above equation should be considered:

- The R<sub>DS(ON)</sub> of low-side MOSFET is varied by temperature and gate to source voltage. Users should determine the maximum R<sub>DS(ON)</sub> by using the manufacturer's datasheet.
- The minimum  $I_{\text{OCSET}}$  ( $9\infty A$ ) and minimum  $R_{\text{OCSET}}$  should be used in the above equation.
- Note that the ILIMIT is the current flow through the lowside MOSFET; ILIMIT must be greater than valley inductor current which is output current minus the half of inductor ripple current.

$$|\mathsf{LIMIT} > \mathsf{IOUT}(\mathsf{MAX}) \square \qquad \frac{\square \mathsf{I}}{2}$$

Where  $\Box I$  = output inductor ripple current

 The overshoot and transient peak current also should be considered.

# **Function Description (Cont.)**

### **Under-Voltage Protection**

The under-voltage function monitors the voltage on FB ( $V_{FB}$ ) by Under-Voltage (UV) comparator to protect the PWM converter against short-circuit conditions. When the  $V_{FB}$  falls below the falling UVP threshold (50%  $V_{REF}$ ), a fault signal is internally generated and the device turns off highside and low-side MOSFETs. The device will enters hiccup mode until the under-voltage phenomenon is released.

### Over-Voltage Protection (OVP) of the PWM Converter

The over-voltage protection monitors the FB voltage to prevent the output from over-voltage condition. When the output voltage rises above 125% of the nominal output voltage, the JTMA8722 turns off the high-side MOSFET and turns on the low-side MOSFET until the output voltage falls below the falling below 105%, the OVP comparator is disengaged and both high-side and low-side drivers turn off.

This OVP scheme only clamps the voltage overshoot and does not invert the output voltage when otherwise activated with a continuously high output from low-side MOSFET driver. It's a common problem for OVP schemes with a latch. Once an over-voltage fault condition is set, it can be reset by releasing COMP or toggling VCC power-on-reset signal.

### Shutdown and Enable

The JTMA8722 can be shut down or enabled by pulling low the voltage on COMP. The COMP is a dual-function pin. During normal operation, this pin represents the output of the error amplifier. It is used to compensate the regulation control loop in combination with the FB pin. Pulling the COMP low (VDISABLE = 0.4V maximum) places the controller into shutdown mode which UGATE and LGATE are pulled to PHASE and GND respectively. When the pull-down device is released, the COMP voltage will start to rise. When the COMP voltage rises above the VDISABLE threshold, the JTMA8722 will begin a new initialization and soft-start process.

# Adaptive Shoot-Through Protection of the PWM Converter

The gate drivers incorporate an adaptive shoot-through protection to prevent high-side and low-side MOSFETs from conducting simultaneously and shorting the input supply. This is accomplished by ensuring the falling gate has turned off one MOSFET before the other is allowed to rise

During turn-off the low-side MOSFET, the LGATE voltage is monitored until it is below 1.5V threshold, at which time the UGATE is released to rise after a constant delay. During turn-off of the high-side MOSFET, the UGATE-to-PHASE voltage is also monitored until it is below 1.5V threshold, at which time the LGATE is released to rise after a constant delay.

# **Application Information**

### **Output Voltage Selection**

The output voltage can be programmed with a resistive divider. Use 1% or better resistors for the resistive divider is recommended. The FB pin is the inverter input of the error amplifier, and the reference voltage is 0.6V. The output voltage is determined by:

Vout = 
$$0.6 \cdot \left[ \frac{1}{1} + \frac{R_1}{R_2} \right]$$

Where R1 is the resistor connected from  $V_{\text{OUT}}$  to FB and R2 is the resistor connected from FB to the GND.

### **Output Capacitor Selection**

The selection of  $C_{\text{OUT}}$  is determined by the required effective series resistance (ESR) and voltage rating rather than the actual capacitance requirement. Therefore, selecting high performance low ESR capacitors is intended for switching regulator applications. In some applications, multiple capacitors have to be paralleled to achieve the desired ESR value. If tantalum capacitors are used, make sure they are surge tested by the manufactures. If in doubt, consult the capacitors manufacturer.

### **Input Capacitor Selection**

The input capacitor is chosen based on the voltage rating and the RMS current rating. For reliable operation, select the capacitor voltage rating to be at least 1.3 times higher than the maximum input voltage. The maximum RMS current rating requirement is approximately lout/2 where lout is the load current. During power up, the input capacitors have to handle large amount of surge current. If tantalum capacitors are used, make sure they are surge tested by the manufactures. If in doubt, consult the capacitors manufacturer.

For high frequency decoupling, a ceramic capacitor between  $0.1 \infty F$  to  $1 \infty F$  can connect between VCC and ground pin.

### **Inductor Selection**

The inductance of the inductor is determined by the output voltage requirement. The larger the inductance, the lower the inductor's current ripple. This will translate into lower output ripple voltage. The ripple current and ripple voltage can be approximated by:

$$\mathsf{IRIPPLE} = \quad \frac{\mathsf{Vin} \; \mathsf{I} \; \mathsf{Vout} \quad \mathsf{V}}{\mathsf{Fsw} \cdot \mathsf{L}} \cdot \frac{\mathsf{OUT}}{\mathsf{Vin}}$$

where Fs is the switching frequency of the regulator.

$$\Box V_{OUT} = I_{RIPPLE} \times ESR$$

A tradeoff exists between the inductor's ripple current and the regulator load transient response time. A smaller inductor will give the regulator a faster load transient response at the expense of higher ripple current and vice versa. The maximum ripple current occurs at the maximum input voltage. A good starting point is to choose the ripple current to be approximately 30% of the maximum output current.

Once the inductance value has been chosen, selecting an inductor is capable of carrying the required peak current without going into saturation. In some types of inductors, especially core that is make of ferrite, the ripple current will increase abruptly when it saturates. This will result in a larger output ripple voltage.

### **PWM Compensation**

The output LC filter of a step down converter introduces a double pole, which contributes with -40dB/decade gain slope and 180 degrees phase shift in the control loop. A compensation network among COMP, FB, and Vout should be added. The compensation network is shown in Figure 5. The output LC filter consists of the output inductor and output capacitors. The transfer function of the LC filter is given by:

$$\mathsf{FESR} = \frac{1}{2 \cdot \Box \cdot \mathsf{ESR} \cdot \mathsf{Cout}}$$

The  $F_{LC}$  is the double poles of the LC filter, and  $F_{ESR}$  is the zero introduced by the ESR of the output capacitor.

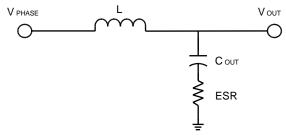


Figure 2. The Output LC Filter

# **Application Information(Cont.)**

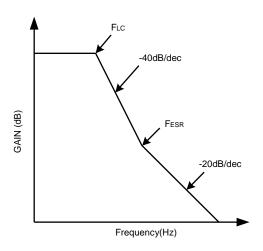


Figure 3. The LC Filter GAIN and Frequency

The PWM modulator is shown in Figure 4. The input is the output of the error amplifier and the output is the PHASE node. The transfer function of the PWM modulator is given by:

Figure 4. The PWM Modulator

The compensation network is shown in Figure 5. It provides a close loop transfer function with the highest zero crossover frequency and sufficient phase margin. The transfer function of error amplifier is given by:

$$\begin{aligned} & \mathsf{GAIN_{AMP}} &= \frac{\frac{1}{|\mathsf{Vout}|} = \frac{\frac{1}{|\mathsf{Volt}|} / |\mathsf{R2} + \frac{1}{|\mathsf{C3}|}|}{\mathsf{R1} / |\mathsf{R3} + \frac{1}{\mathsf{sC3}}|} \\ & = \frac{\mathsf{R1} + \mathsf{R3}}{\mathsf{R1} \cdot \mathsf{R3} \cdot \mathsf{C1}} \cdot \frac{\left\{ s + \frac{1}{\mathsf{R2} \cdot \mathsf{C2}} \right\} / |\mathsf{S} + \frac{1}{\mathsf{R3} \cdot \mathsf{C3}}|}{\mathsf{S} \cdot \mathsf{S} + \frac{\mathsf{C1} \cdot \mathsf{C2}}{\mathsf{C3}} / |\mathsf{S} + \frac{\mathsf{C3} \cdot \mathsf{C3}}{\mathsf{S}} / |\mathsf{C3} / |\mathsf{C3}} \end{aligned}$$

The poles and zeros of the transfer function are:

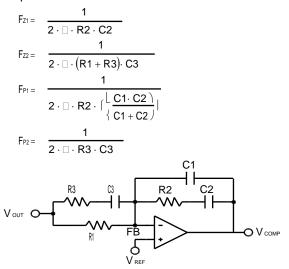


Figure 5. Compensation Network

The closed loop gain of the converter can be written as:

Figure 6. shows the asymptotic plot of the closed loop converter gain, and the following guidelines will help to design the compensation network. Using the below guidelines should give a compensation similar to the curve plotted. A stable closed loop has a -20dB/ decade slope and a phase margin greater than 45 degree.

- 1. Choose a value for R1, usually between 1K and 5K.
- 2. Select the desired zero crossover frequency

Use the following equation to calculate R2:

R2= 
$$\frac{\Box V_{OSC}}{V_{IN}} \cdot \frac{F}{F_{LC}}$$

3. Place the first zero  $F_{Z1}$  before the output LC filter double pole frequency  $F_{LC}$ .

$$F_{Z1} = 0.75 X F_{LC}$$

Calculate the C2 by the equation:

$$C2 = \frac{1}{2 \cdot \Box \cdot R2 \cdot F_{1} \cdot C \cdot 0.75}$$

# **Application Information(Cont.)**

4. Set the pole at the ESR zero frequency FESR:

Calculate the C1 by the equation:

C1= 
$$\frac{C2}{2 \cdot \Box \cdot R2 \cdot C2 \cdot F_{ESR} \Box 1}$$

5. Set the second pole  $F_{P2}$  at the half of the switching frequency and also set the second zero  $F_{Z2}$  at the output LC filter double pole  $F_{LC}$ . The compensation gain should not exceed the error amplifier open loop gain, check the compensation gain at  $F_{P2}$  with the capabilities of the error amplifier.

$$F_{P2} = 0.5 X F_{S}$$

$$F_{Z2} = F_{LC}$$

Combine the two equations will get the following component calculations:

$$GAINLC = \frac{1 + s \cdot ESR \cdot Cout}{s \cdot L \cdot Cout + s \cdot ESR \cdot Cout + 1}$$

The poles and zero of this transfer functions are:

Fig = 
$$\frac{1}{2 \cdot \Box \cdot L \sqrt{Cour}}$$

$$R3 = \frac{R1}{\frac{Fs}{2 \cdot Fic}} \Box 1$$

$$C3 = \frac{1}{\frac{B^2}{2^2}} \frac{Fs}{5}$$

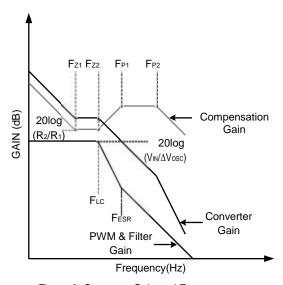


Figure 6. Converter Gain and Frequency

### **MOSFET Selection**

The selection of the N-channel power MOSFETs is determined by the R<sub>DS(ON)</sub>, reverse transfer capacitance (C<sub>RSS</sub>), and maximum output current requirement. The losses in the MOSFETs have two components: conduction loss and transition loss. For the upper and lower MOSFET, the losses are approximately given by the following equations:

$$P_{\text{UPPER}} = I_{\text{OUT2}} \; (1 + \; TC) (R_{\text{DS(ON)}}) D \; + \; (0.5) (I_{\text{out}}) (V_{\text{IN}}) (t_{\text{sw}}) F_{\text{SW}}$$

$$P_{LOWER} = I_{OUT2} (1 + TC)(R_{DS(ON)})(1-D)$$

where lout is the load current

TC is the temperature dependency of RDS(ON)

Fsw is the switching frequency

 $t_{\mbox{\tiny SW}}$  is the switching interval

D is the duty cycle

Note that both MOSFETs have conduction losses while the upper MOSFET includes an additional transition loss.

The switching internal,  $t_{sw}$ , is the function of the reverse transfer capacitance  $C_{\text{RSS}}$ . Figure 7 illustrates the switching waveform internal of the MOSFET.

The (1+TC) term factors in the temperature dependency of the  $R_{DS(ON)}$  and can be extracted from the " $R_{DS(ON)}$  vs Temperature" curve of the power MOSFET.

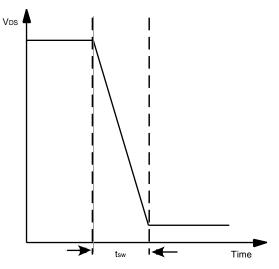


Figure 7. Switching Waveform Across MOSFET

# **Application Information (Cont.)**

### **Layout Consideration**

In any high switching frequency converter, a correct layout is important to ensure proper operation of the regulator. With power devices switching at 300kHz,the resulting current transient will cause voltage spike across the interconnecting impedance and parasitic circuit elements. As an example, consider the turn-off transition of the PWM MOSFET. Before turn-off, the MOSFET is carrying the full load current. During turn-off, current stops flowing in the MOSFET and is free-wheeling by the lower MOSFET and parasitic diode. Any parasitic inductance of the circuit generates a large voltage spike during the switching interval. In general, using short and wide printed circuit traces should minimize interconnecting imped ances and the magnitude of voltage spike. And signal and power grounds are to be kept separate till combined using ground plane construction or single point grounding. Figure 8. illustrates the layout, with bold lines indicating high current paths; these traces must be short and wide. Components along the bold lines should be placed lose together. Below is a checklist for your layout:

- Keep the switching nodes (UGATE, LGATE, and PHASE) away from sensitive small signal nodes since these nodes are fast moving signals. Therefore, keep traces to these nodes as short as possible.
- The traces from the gate drivers to the MOSFETs (UG and LG) should be short and wide.
- Place the source of the high-side MOSFET and the drain of the low-side MOSFET as close as possible. Minimizing the impedance with wide layout plane between the two pads reduces the voltage bounce of the node.
- Decoupling capacitor, compensation component, the resistor dividers, and boot capacitors should be close their pins. (For example, place the decoupling ceramic capacitor near the drain of the high-side MOSFET as close as possible. The bulk capacitors are also placed near the drain).
- The input capacitor should be near the drain of the upper MOSFET; the output capacitor should be near the loads. The input capacitor GND should be close to the output capacitor GND and the lower MOSFET GND.

- The drain of the MOSFETs ( $V_{\text{IN}}$  and PHASE nodes) should be a large plane for heat sinking.
- The Rocset resistance should be placed near the IC as close as possible.

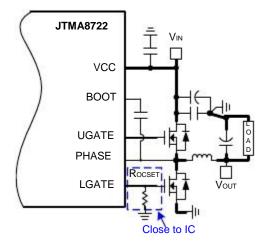
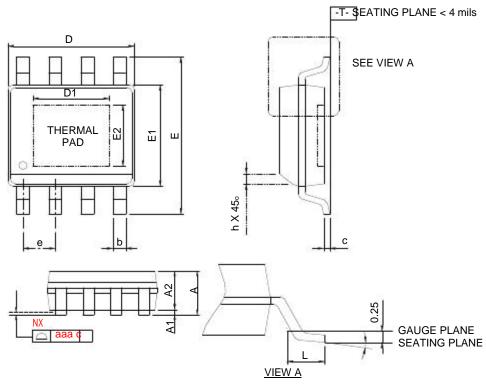


Figure 8. Layout Guidelines

# **Package Information**

SOP-8P



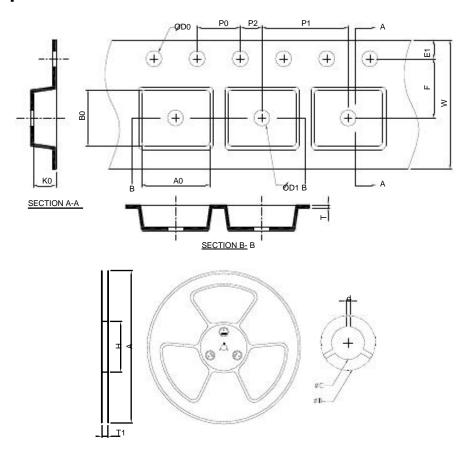
S		SOF	P-8P	
%> <u>₹</u>	MILLIM	ETERS	INCH	ES
Ď	MIN.	MAX.	MIN.	MAX.
Α		1.60		0.063
A1	0.00	0.15	0.000	0.006
A2	1.25		0.049	
b	0.31	0.51	0.012	0.020
С	0.17	0.25	0.007	0.010
D	4.80	5.00	0.189	0.197
D1	2.50	3.50	0.098	0.138
E	5.80	6.20	0.228	0.244
E1	3.80	4.00	0.150	0.157
E2	2.00	3.00	0.079	0.118
е	1.27	BSC	0.050	BSC
h	0.25	0.50	0.010	0.020
L	0.40	1.27	0.016	0.050
0	0°C	8°C	0°C	8°C
aaa	0.	10	0.00	4

Note: 1. Followed from JEDEC MS-012 BA.

Dimension "D" does not include mold flash, protrusions or gate burrs.
 Mold flash, protrusion or gate burrs shall not exceed 6 mil per side.

<sup>3.</sup> Dimension "E" does not include inter-lead flash or protrusions. Inter-lead flash and protrusions shall not exceed 10 mil per side.

# **Carrier Tape & Reel Dimensions**



Application	Α	Н	T1	С	d	D	W	E1	F
222.05	330.0±2.00	50 MIN.	12.4 <b>+</b> 2.00 -0.00	13.0+0.50 -0.20	1.5 MIN.	20.2 MIN.	12.0±0.30	1.75±0.10	5.5±0.05
SOP-8P	P0	P1	P2	D0	D1	Т	A0	В0	K0
	4.0±0.10	8.0±0.10	2.0±0.05	1.5+0.10 -0.00	1.5 MIN.	0.6+0.00 -0.40	6.40±0.20	5.20±0.20	2.10±0.20

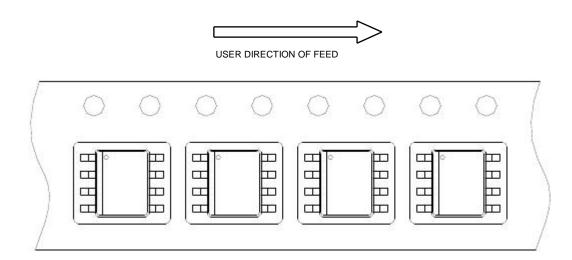
(mm)

# **Devices Per Unit**

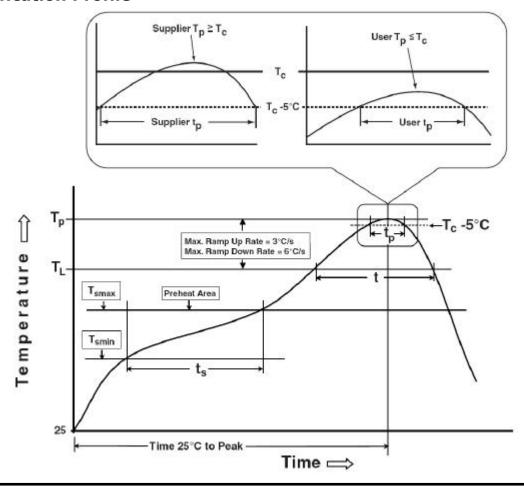
Package Type	Unit	Quantity	
SOP-8P	Tape & Reel	2500	

# **Taping Direction Information**

SOP-8



# **Classification Profile**



### **Classification Reflow Profiles**

Profile Feature	Sn-Pb Eutectic Assembly	Pb-Free Assembly
Preheat & Soak Temperature min (Tsmin) Temperature max (Tsmax) Time (Tsmin to Tsmax) (ts)	100 °C 150 °C 60-120 seconds	150 °C 200 °C 60-120 seconds
Average ramp-up rate (Tsmax to Tp)	3 °C/second max.	3 °C/second max.
Liquidous temperature (TL) Time at liquidous (tL)	183 °C 60-150 seconds	217 °C 60-150 seconds
Peak package body Temperature (T <sub>P</sub> )*	See Classification Temp in table 1	See Classification Temp in table 2
Time (t <sub>P</sub> )** within 5°C of the specified classification temperature (T <sub>c</sub> )	20** seconds	30** seconds
Average ramp-down rate (Tp to Tsmax)	6 °C/second max.	6 °C/second max.
Time 25°C to peak temperature	6 minutes max.	8 minutes max.

<sup>\*</sup> Tolerance for peak profile Temperature (Tp) is defined as a supplier minimum and a user maximum.

Table 1. SnPb Eutectic Process – Classification Temperatures (Tc)

Package Thickness	Volume mm <sup>3</sup> <350	Volume mm <sup>3</sup> ε350
<2.5 mm	235 °C	220 °C
ε2.5 mm	220 °C	220 °C

Table 2. Pb-free Process – Classification Temperatures (Tc)

Package Thickness	Volume mm <sup>3</sup> <350	Volume mm <sup>3</sup> 350-2000	Volume mm <sup>3</sup> >2000
<1.6 mm	260 °C	260 °C	260 °C
1.6 mm – 2.5 mm	260 °C	250 °C	245 °C
ε2.5 mm	250 °C	245 °C	245 °C

# **Reliability Test Program**

Test item	Method	Description
SOLDERABILITY	JESD-22, B102	5 Sec, 245°C
HOLT	JESD-22, A108	1000 Hrs, Bias @ T <sub>i</sub> =125°C
PCT	JESD-22, A102	168 Hrs, 100%RH, 2atm, 121°C
TCT	JESD-22, A104	500 Cycles, -65°C~150°C
НВМ	MIL-STD-883-3015.7	VHBM≧2KV
MM	JESD-22, A115	VMM≧200V
Latch-Up	JESD 78	10ms, 1tr≥100mA

<sup>\*\*</sup> Tolerance for time at peak profile temperature (tp) is defined as a supplier minimum and a user maximum.

# **JTMA8722/A/B/C/D**

**Customer Service** 

2: